

# PSMN8R0-80YL

N-channel 80 V, 8 m $\Omega$  logic level MOSFET in LFPAK56

**Product data sheet** 

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

#### **Features and benefits** 2.

- Advanced TrenchMOS provides low R<sub>DSon</sub> and low gate charge
- Logic level gate operation
- Avalanche rated, 100% tested
- LFPAK provides maximum power density in a Power SO8 package

#### **Applications** 3.

- Synchronous rectification in power supply equipment
- Chargers & adaptors with V<sub>out</sub> < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

#### Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                        | Conditions  |     | Min | Тур  | Max | Unit |
|-------------------------|----------------------------------|---|-----|-----|------|-----|------|
| V <sub>DS</sub>         | drain-source voltage             | 25 °C ≤ T <sub>j</sub> ≤ 175 °C   |     | -   | -    | 80  | V    |
| I <sub>D</sub>          | drain current                    | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>   | [1] | -   | -    | 100 | Α    |
| P <sub>tot</sub>        | total power dissipation          | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>  |     | -   | -    | 238 | W    |
| Static characte         | Static characteristics           |   |     |     |      |     |      |
| R <sub>DSon</sub>       | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$  |     | -   | 6.3  | 8.5 | mΩ   |
| Dynamic characteristics |                                  |   |     |     |      |     |      |
| $Q_{GD}$                | gate-drain charge                | $I_D = 25 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$<br>$T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$ |     | -   | 17.1 | -   | nC   |

[1] Continuous current is limited by package.



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# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                         | Graphic symbol |
|-----|--------|-----------------------------------|--|----------------|
| 1   | S      | source                            | mb   | D              |
| 2   | S      | source                            |  |                |
| 3   | S      | source                            | q  | G_U: 4         |
| 4   | G      | gate                              | و ق ق ق                                    | mbb076 S       |
| mb  | D      | mounting base; connected to drain | 1 2 3 4<br>LFPAK56; Power-<br>SO8 (SOT669) |                |

# 6. Ordering information

Table 3. Ordering information

| Type number  | Package               |  |         |  |  |
|--------------|-----------------------|--|---------|--|--|
|              | Name                  | Description  | Version |  |  |
| PSMN8R0-80YL | LFPAK56;<br>Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669  |  |  |

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions   |     | Min | Max | Unit |
|------------------|-------------------------|--|-----|-----|-----|------|
| $V_{DS}$         | drain-source voltage    | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                |     | -   | 80  | V    |
| $V_{DGR}$        | drain-gate voltage      | $R_{GS}$ = 20 k $\Omega$                                       |     | -   | 80  | V    |
| $V_{GS}$         | gate-source voltage     |  |     | -20 | 20  | V    |
| P <sub>tot</sub> | total power dissipation | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                         |     | -   | 238 | W    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>  | [1] | -   | 100 | Α    |
|                  |                         | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u> | [1] | -   | 75  | Α    |
| I <sub>DM</sub>  | peak drain current      | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3 |     | -   | 423 | Α    |
| T <sub>stg</sub> | storage temperature     |  |     | -55 | 175 | °C   |
| Tj               | junction temperature    |  |     | -55 | 175 | °C   |
| Source-drain     | diode                   |  | '   | '   |     |      |
| Is               | source current          | T <sub>mb</sub> = 25 °C  | [1] | -   | 100 | Α    |
| I <sub>SM</sub>  | peak source current     | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$       |     | -   | 423 | Α    |

### N-channel 80 V, 8 mΩ logic level MOSFET in LFPAK56

| Symbol               | Parameter                                    | Conditions   |        | Min | Max | Unit |
|----------------------|--|--|--------|-----|-----|------|
| Avalanche rug        | gedness                                      |  |        |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $I_D$ = 100 A; $V_{sup}$ ≤ 80 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4 | [2][3] | -   | 148 | mJ   |

- [1]
- Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}\text{C}.$
- Refer to application note AN10273 for further information.

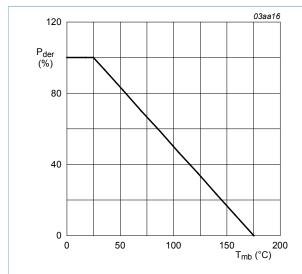
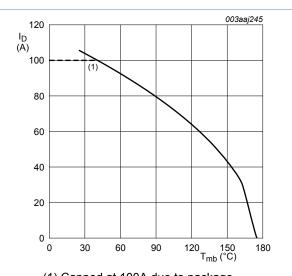


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

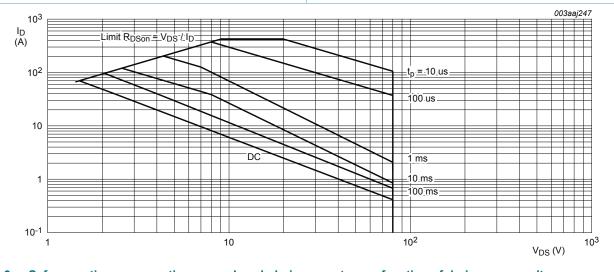
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



(1) Capped at 100A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$



Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb}$  = 25°C;  $I_{DM}$  is a single pulse

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#### N-channel 80 V, 8 m $\Omega$ logic level MOSFET in LFPAK56

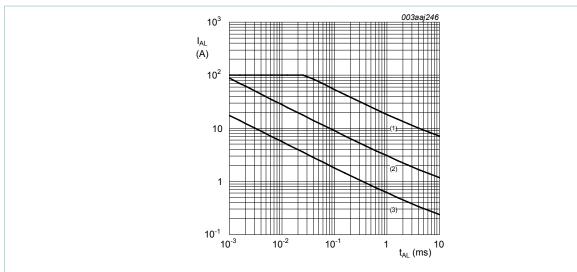


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) 
$$T_{j(init)} = 25$$
°C; (2)  $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

### 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol                | Parameter   | Conditions | Min | Тур | Max  | Unit |
|-----------------------|---|------------|-----|-----|------|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | Fig. 5     | -   | -   | 0.63 | K/W  |

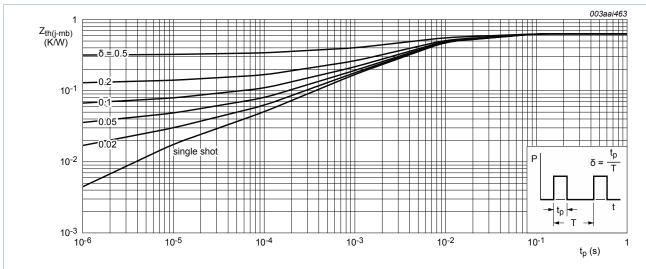


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

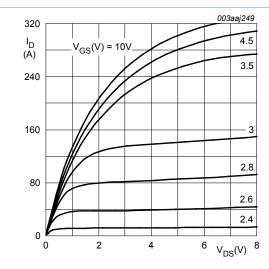
## 9. Characteristics

Table 6. Characteristics

| Symbol               | Parameter                     | Conditions  | Min | Тур  | Max  | Unit |
|----------------------|-------------------------------|---|-----|------|------|------|
| Static char          | acteristics                   |   |     |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source                  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C  | 80  | -    | -    | V    |
|                      | breakdown voltage             | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C   | 72  | -    | -    | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage | $I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = 25 \text{ °C; } Fig. 9;$<br>Fig. 10  | 1.4 | 1.7  | 2.1  | V    |
|                      |                               | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$   | -   | -    | 2.45 | V    |
|                      |                               | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; Fig. 9$   | 0.5 | -    | -    | V    |
| I <sub>DSS</sub>     | drain leakage current         | V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C  | -   | -    | 500  | μA   |
|                      |                               | V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | 0.07 | 10   | μA   |
| I <sub>GSS</sub>     | gate leakage current          | V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | 2    | 100  | nA   |
|                      |                               | V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>    | drain-source on-state         | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>  | -   | 6.3  | 8.5  | mΩ   |
| resistance           |                               | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C;<br>Fig. 11   | -   | 5.8  | 8    | mΩ   |
|                      |                               | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C;<br>Fig. 11; Fig. 12  | -   | -    | 21.3 | mΩ   |
| Dynamic cl           | haracteristics                |   | l l |      |      |      |
| Q <sub>G(tot)</sub>  | total gate charge             | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V;<br>T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> | -   | 104  | -    | nC   |
|                      |                               | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 5 V;   | -   | 54.7 | -    | nC   |
| $Q_{GS}$             | gate-source charge            | T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>   | -   | 13.5 | -    | nC   |
| $Q_GD$               | gate-drain charge             |   | -   | 17.1 | -    | nC   |
| C <sub>iss</sub>     | input capacitance             | V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;   | -   | 6125 | 8167 | pF   |
| C <sub>oss</sub>     | output capacitance            | T <sub>j</sub> = 25 °C; <u>Fig. 15</u>  | -   | 397  | 476  | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance  |   | -   | 207  | 284  | pF   |
| t <sub>d(on)</sub>   | turn-on delay time            | $V_{DS}$ = 60 V; $R_L$ = 2.4 $\Omega$ ; $V_{GS}$ = 5 V;   | -   | 28   | -    | ns   |
| t <sub>r</sub>       | rise time                     | $R_{G(ext)} = 5 \Omega$ ; $T_j = 25 ^{\circ}C$  | -   | 50   | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time           |   | -   | 82   | -    | ns   |
| t <sub>f</sub>       | fall time                     |   | -   | 45   | -    | ns   |
| Source-dra           | in diode                      |   | l l |      | 1    | J    |
| $V_{SD}$             | source-drain voltage          | I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C; <u>Fig. 16</u>  | _   | 0.82 | 1.2  | V    |

### N-channel 80 V, 8 m $\Omega$ logic level MOSFET in LFPAK56

| Symbol          | Parameter             | Conditions  | Min | Тур  | Max | Unit |
|-----------------|-----------------------|---|-----|------|-----|------|
| t <sub>rr</sub> | reverse recovery time | $I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | _   | 30.9 | -   | ns   |
| Q <sub>r</sub>  | recovered charge      | $V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$                                      | -   | 36.3 | -   | nC   |



 $T_i = 25 \,^{\circ}\text{C}; t_D = 300 \,\mu\text{s}$ 

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

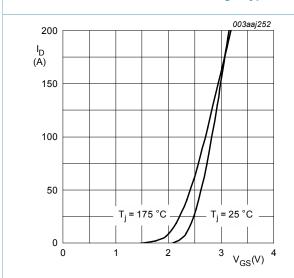


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



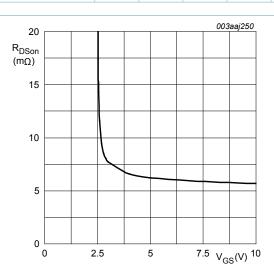


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

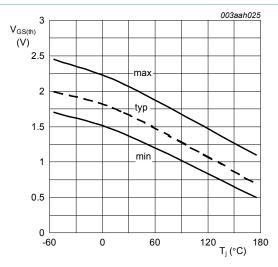


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA;  $V_{DS}$  =  $V_{GS}$ 

### N-channel 80 V, 8 m $\Omega$ logic level MOSFET in LFPAK56

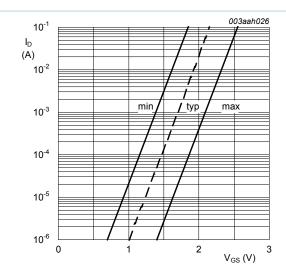


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_i = 25$$
°C;  $V_{DS} = 5V$ 

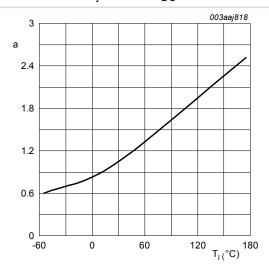
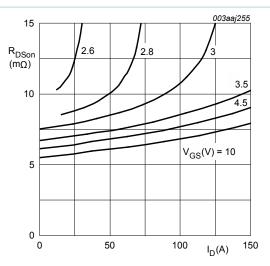


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



$$T_j = 25 \, ^{\circ}\text{C}; t_p = 300 \, \mu\text{s}$$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

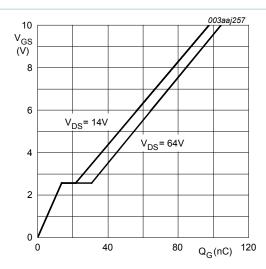


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_i = 25$$
°C;  $I_D = 25A$ 

### N-channel 80 V, 8 m $\Omega$ logic level MOSFET in LFPAK56

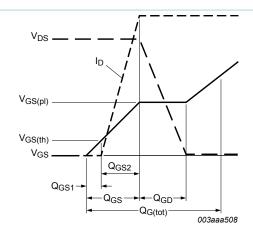


Fig. 14. Gate charge waveform definitions

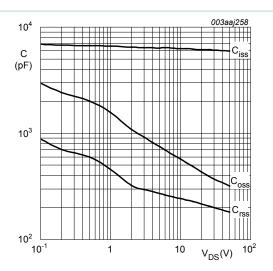


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
;  $f = 1MHz$ 

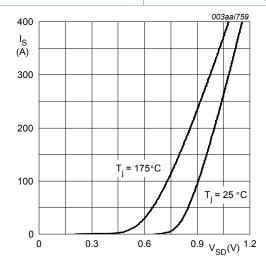
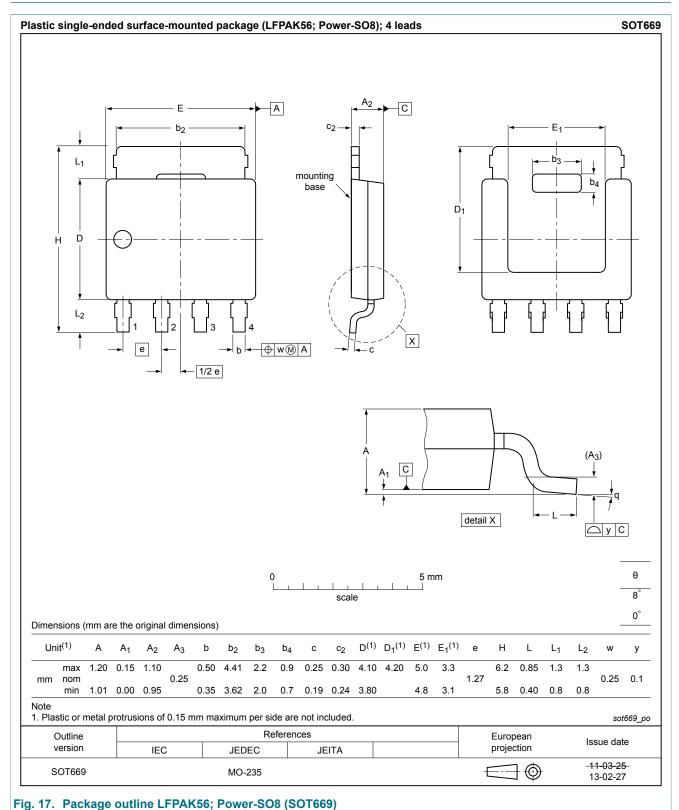


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

## 10. Package outline



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#### N-channel 80 V, 8 mΩ logic level MOSFET in LFPAK56

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|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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